

**60V/2A, Common Anode Step-Down LED Driver****Features**

- Maximum 2A constant output current
- >95% efficiency @ input voltage 36V, load condition: 2A, 10 LEDs
- 4.5V~60V wide input voltage range
- Common anode connection
- Adaptive hysteretic PFM with adjustable fixed frequency operation
- Tunable output current
- Integrated power switch with 0.2Ω on-resistance
- Full protections: UVLO/OCP/ Thermal/ LED Open-/ LED Short- Circuited

**Product Description**

MBI6662 is a high efficiency, constant current and step-down DC/DC converter. It is designed to deliver constant current to light up high power LEDs. With the adaptive hysteretic PFM control scheme, MBI6662 can achieve constant frequency operation under common anode connection.

The output current of MBI6662 can be set by an external resistor, and LED brightness can be controlled via a pulse width modulation (PWM) signal through DIM pin. In addition, the soft-start function limits the inrush current while the power is turned on. MBI6662 also features under voltage lock out (UVLO), over temperature protection (OTP), and over current protection (OCP) to ensure system robustness and prevent IC and LEDs from being damaged once any abnormal condition occurs.

To ensure system reliability, MBI6662 is equipped with thermal shutdown protection (TSD), which protects IC from overheating by turning off the internal MOSFET. MBI6662 is available in thermal-enhanced DFN-10 and SOP-10 package to handle power dissipation more efficiently.

**Applications**

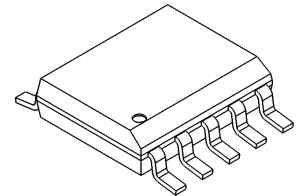
- Stage Lighting
- High Power LED Wall-Washer
- Automotive LED Lighting
- Parallel Lighting Fixtures Connected by Common-Anode Scheme

Dual Flat No-lead



GDF: DFN-10L 3\*3

Small Outline Package



GD: SOP-10L-150

Pin Configuration

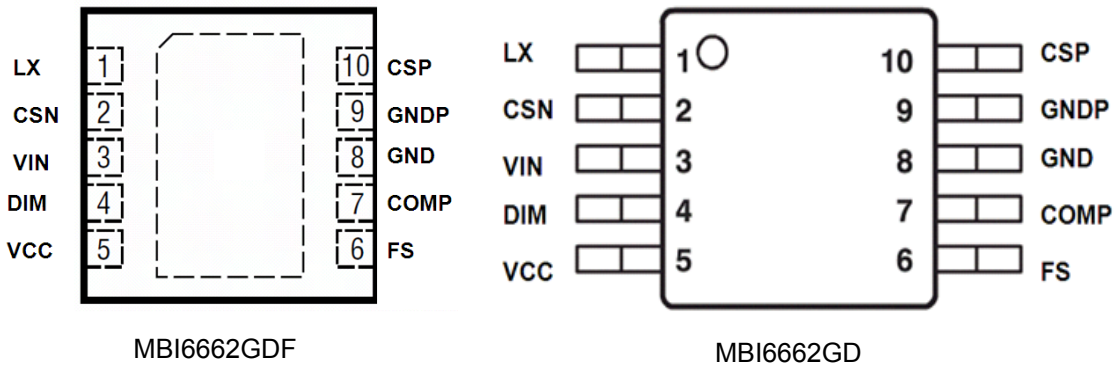


Fig.1 Pin Configuration of MBI6662

Pin Description

Pin Name	Function
LX	Terminal of the drain node of the internal N-MOSFET
CSN	Terminal to sense schottky diode current
VIN	Terminal of the supply voltage
DIM	Terminal of the PWM dimming input
VCC	Terminal of the Internal regulator output
FS	Terminal of the swtiching frequency setting resistor
COMP	Terminal of the compensator
GND	Terminal of the analog signal ground
GNDP	Terminal of the power signal ground
CSP	Terminal of the current sensing resistor

\*To improve the noise immunity, the thermal pad is suggested to connect to GND on PCB. In addition, when a heat-conducting copper foil on PCB is soldered with thermal pad, the desired thermal conductivity will be improved.

Typical Application Circuit

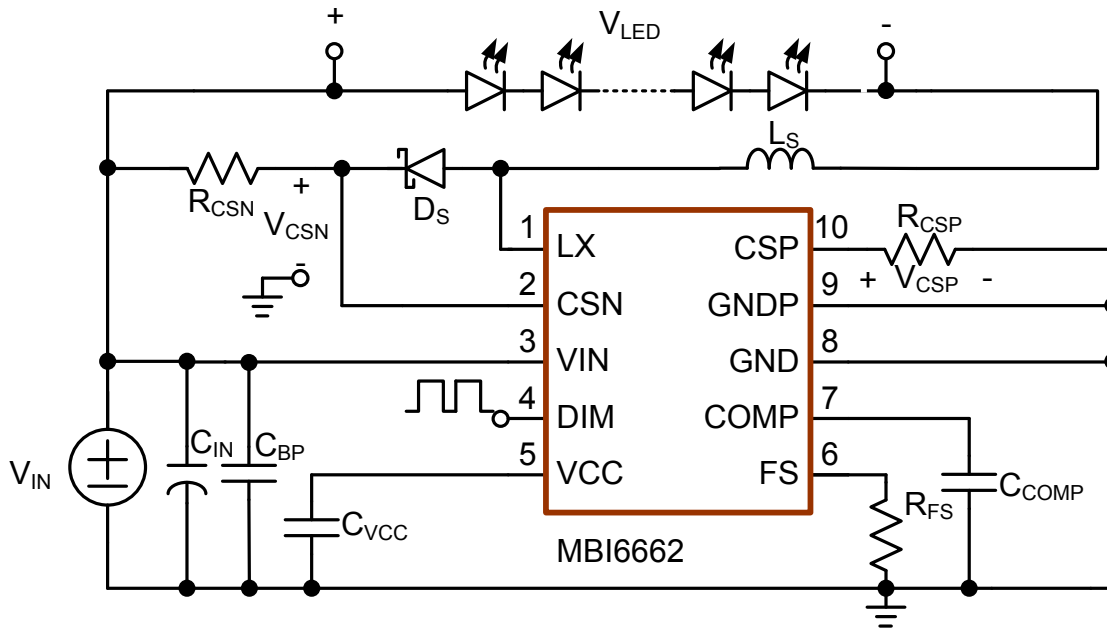


Fig.2 Typical application circuit of MBI6662

Functional Diagram

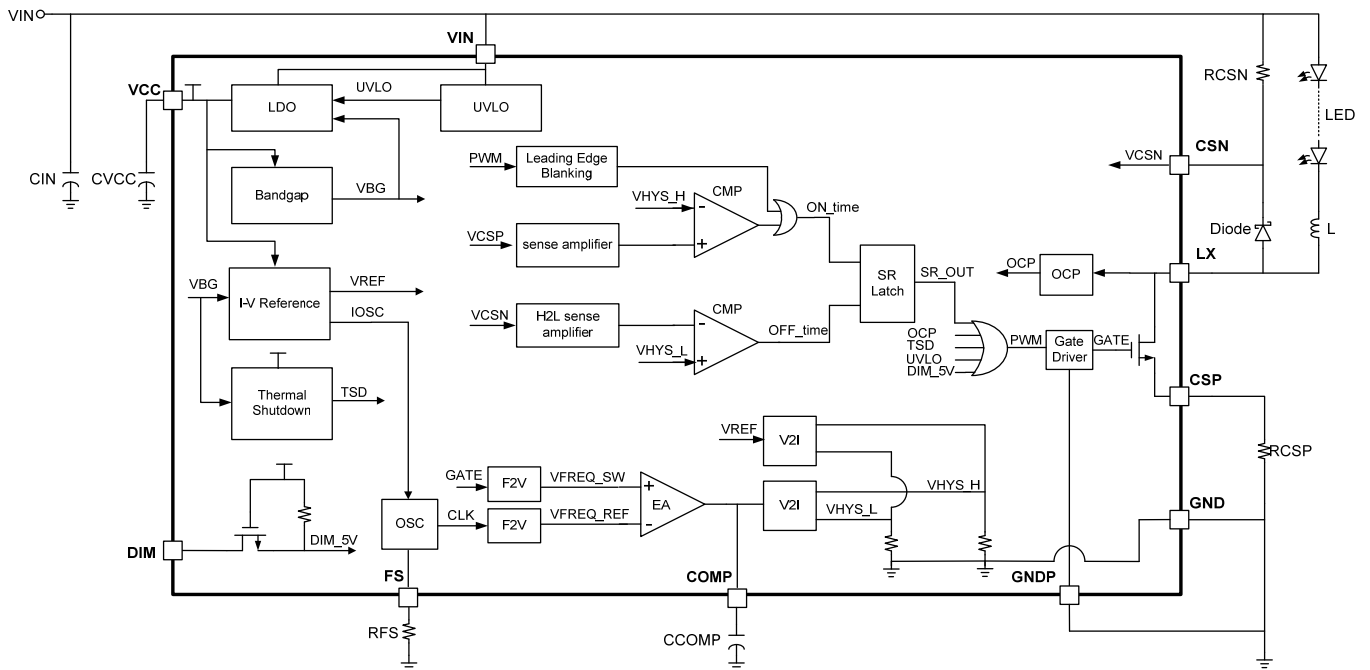


Fig. 3 Functional diagram of MBI6662

Maximum Ratings

Operation above the maximum ratings may cause device failure.

Characteristic		Symbol	Rating	Unit
Supply Voltage		$V_{IN}$	-0.3~75	V
Sustaining Voltage at DIM pin		$V_{DIM}$	-0.3~75	V
Sustaining Voltage at LX pin		$V_{LX}$	-0.3~75	V
Sustaining Voltage at CSN pin		$V_{CSN}$	-0.3~75	V
Sustaining Voltage at CSP pin		$V_{CSP}$	-0.3~7	V
Sustaining Voltage at VCC pin		$V_{CC}$	-0.3~7	V
Sustaining Voltage at COMP pin		$V_{COMP}$	-0.3~7	V
Sustaining Voltage at FS pin		$V_{FS}$	-0.3~7	V
Power Dissipation (On 4 Layer PCB, $T_a=25^{\circ}C$ )*	GDF Type	$P_D$	2.67	W
Thermal Resistance (By simulation, on 4 Layer PCB)*		$R_{th(j-a)}$	47.85	$^{\circ}C/W$
Power Dissipation (On 4 Layer PCB, $T_a=25^{\circ}C$ )*	GD Type	$P_D$	3.13	W
Thermal Resistance (By simulation, on 4 Layer PCB)*		$R_{th(j-a)}$	40	$^{\circ}C/W$
Junction Temperature		$T_{j,max}$	150***	$^{\circ}C$
Operating Ambient Temperature		$T_{opr}$	-40~+85	$^{\circ}C$
Storage Temperature		$T_{stg}$	-55~+150	$^{\circ}C$

\*The PCB size is 76.2mm\*114.3mm in simulation. Please refer to JEDEC JESD51.

\*\* Operation at the maximum rating for extended periods may reduce the device reliability; therefore, the suggested operation temperature of the device ( $T_{opr}$ ) is under 125 $^{\circ}C$ .

Note: The performance of thermal dissipation is strongly related to the size of thermal pad, thickness and layer numbers of the PCB. The empirical thermal resistance may be different from simulative value. Users should plan for expected thermal dissipation performance by selecting package and arranging layout of the PCB to maximize the capability.

Electrical Characteristics

Test condition:  $V_{IN}=12V$ ,  $V_{OUT}=3.6V$ ,  $L1=68\mu H$ ,  $C_{IN}=C_{OUT}=10\mu F$ ,  $C_{VCC}=1\mu F$ ,  $T_A=25^\circ C$ ; unless otherwise specified.

Characteristics	Symbol	Condition	Min.	Typ.	Max.	Unit
<b>DC Characteristics</b>						
Supply Voltage	$V_{IN}$	-	4.5	-	60	V
Supply Current	$I_{DD}$	$V_{IN}=4.5V\sim 60V$ , $F_{SW}=100kHz$	-	1.5	2.5	mA
Output Current	$I_{OUT}$	Refer to page 19 for derating.	-	-	2.0	A
Output Current Accuracy	$dI_{OUT}/I_{OUT}$	$0.35A \leq I_{OUT} \leq 2A$	-	$\pm 2$	$\pm 5$	%
MOSFET On-Resistance	$R_{DS,ON}$	$I_{OUT}=350mA$	-	0.2	0.5	$\Omega$
MOSFET Leakage	$I_{LEAK}$	$V_{LX}=60V$	-	0.1	1.0	$\mu A$
Efficiency	-	$V_{IN}=36V$ , $I_{OUT}=2A$ , 10LEDs	-	95	-	%
<b>Switching Characteristics</b>						
LX Rise Time	$T_{R,LX}$	-	-	-	20	ns
LX Fall Time	$T_{F,LX}$	-	-	-	20	ns
Recommended Duty Cycle	$D_{LX}$	-	10	-	90	%
Operating Frequency	$F_{SW}$	-	0.1	-	1.0	MHz
<b>Current Sense</b>						
Mean Sense Voltage	$V_{CS}$	-	95	100	105	mV
Low Side Hysteresis	$V_{CSP}$	Normalize to average current	5	-	80	%
High Side Hysteresis	$V_{IN}-V_{CSN}$	Normalize to average current	5	-	80	%
CSP Propagation Delay	$T_{PPD}$	LX tights to $V_{IN}$	-	100	-	ns
CSN Propagation Delay	$T_{NPD}$	LX tights to GND	-	100	-	ns
High Side Blanking Time	$T_{LEB,H}$	-	-	280	-	ns
Low Side Blanking Time	$T_{LEB,L}$	-	-	180	-	ns
<b>Thermal Shutdown (TSD)</b>						
Thermal Shutdown Threshold*	$T_{SD}$	-	145	155	175	$^\circ C$
Thermal Shutdown Hysteresis*	$T_{SD-HYS}$	-	20	30	40	$^\circ C$
<b>Under Voltage Lock-out (UVLO)</b>						
UVLO Voltage	$V_{UVLO}$	$T_A=-40\sim 85^\circ C$	-	4.1	-	V
Start Up Voltage	$V_{STUP}$	-	-	4.4	-	V
<b>Over Current Protection (OCP)</b>						
Over Current Threshold*		-	-	3.0	-	A
<b>PWM Dimming</b>						
PWM Duty Cycle Range	$D_{DIM}$	PWM frequency:0.1kHz~1kHz	1	-	100	%
PWM Signal High Level	$V_{IH,DIM}$	$V_{IN}=4.5V\sim 60V$	2.5	-	-	V
PWM Signal Low Level	$V_{IL,DIM}$	$V_{IN}=4.5V\sim 60V$	-	-	0.8	V
<b>Regulator</b>						
Regulated Voltage	$V_{CC}$	$V_{IN}=4.5V$ , $I_{LOAD}=2mA$	-	4.2	-	V
	$V_{CC}$	$V_{IN}=6V\sim 60V$ , $I_{LOAD}=2mA$	4.5	5.0	5.5	V

\*Parameters are not tested at production. Parameters are guaranteed by design.

Typical Performance Characteristics

Efficiency for Series LED Load/Input Voltage

$R_{CSP}=R_{CSN}=100m\Omega(1A)/66m\Omega(1.5A)/50m\Omega(2A)$ ,  $R_{FS}=300k\Omega$ ,  $L=68\mu H$ ,  $C_{COMP}=4.7nF$ ,  $C_{VCC}=1\mu F$ ,  $C_{IN}=10\mu F$ .

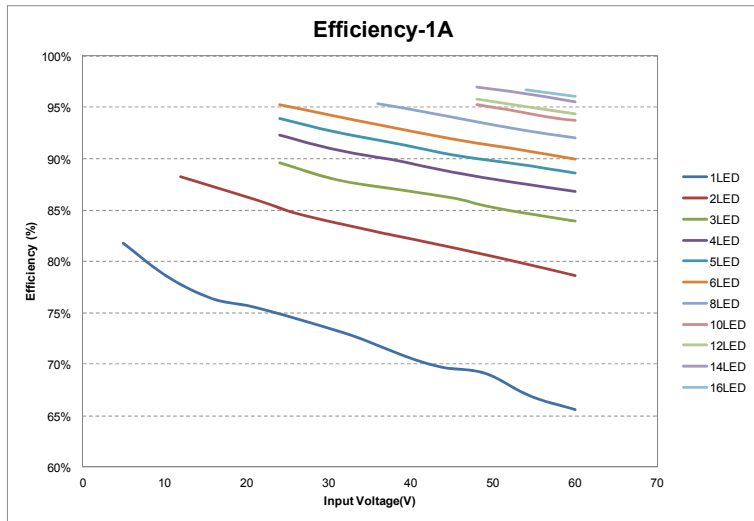


Fig.4 Efficiency of MBI6662: 1A output current

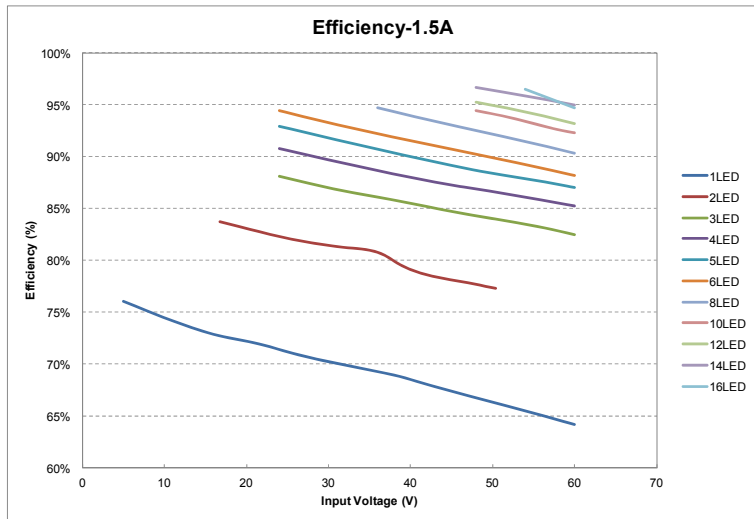


Fig.5 Efficiency of MBI6662: 1.5A output current

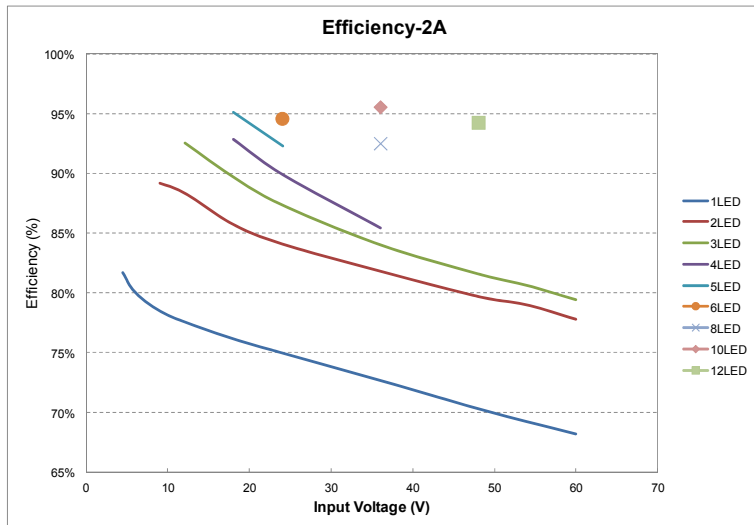


Fig.6 Efficiency of MBI6662: 2A output current

**Output Current vs. Input Voltage (Line Regulation)**

$R_{CSP}=R_{CSN}=100m\Omega(1A)/66m\Omega(1.5A)/50m\Omega(2A)$ ,  $R_{FS}=300k\Omega$ ,  $L=68\mu H$ ,  $C_{COMP}=4.7nF$ ,  $C_{VCC}=1\mu F$ ,  $C_{IN}=10\mu F$ .

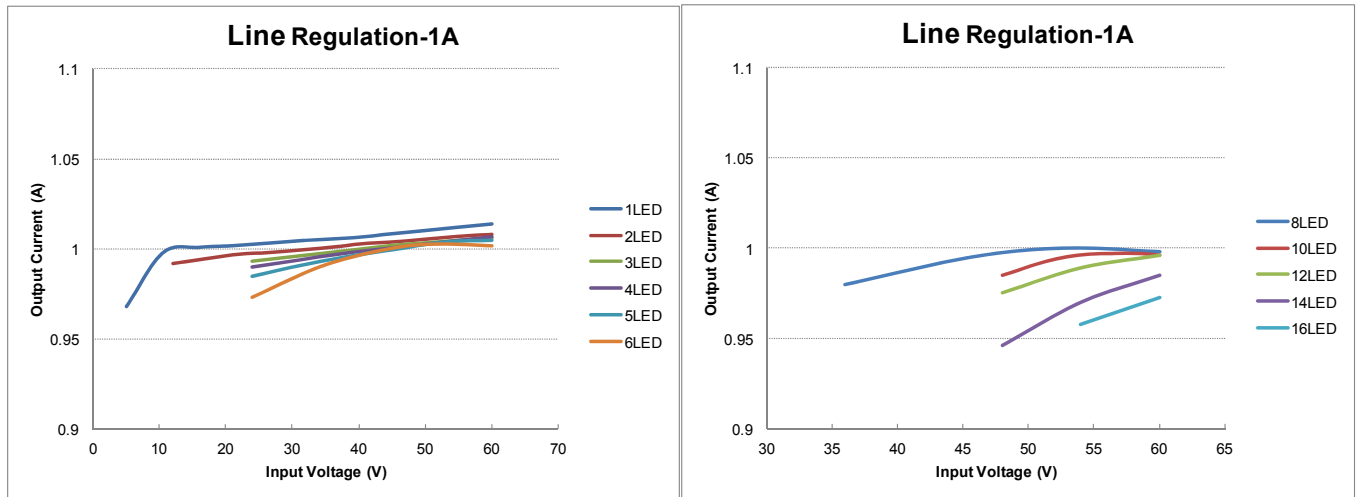


Fig.7 Line regulation of MBI6662: 1A output current

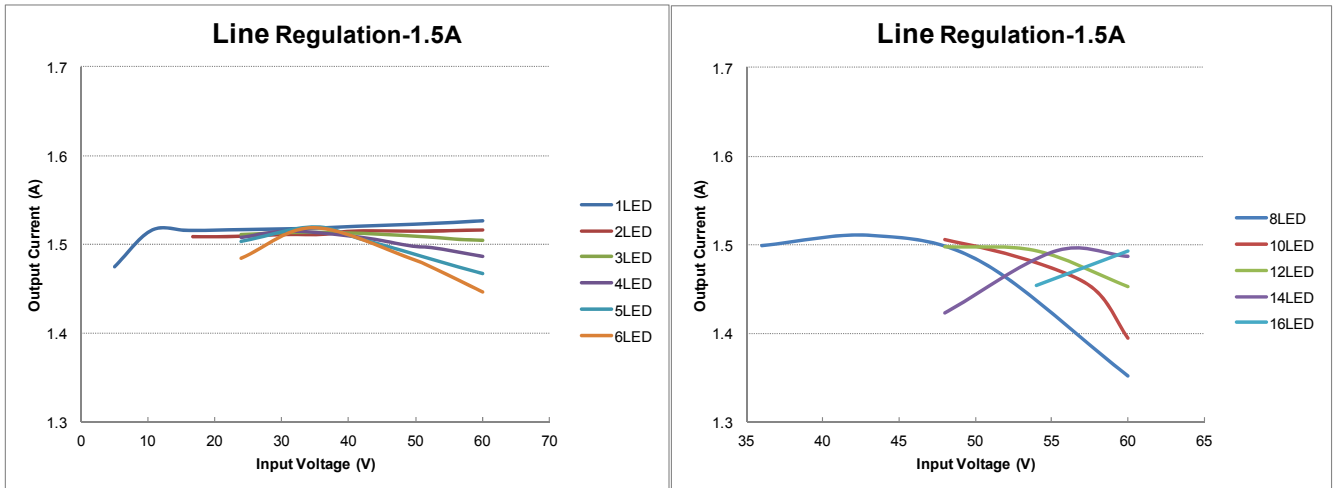


Fig.8 Line regulation of MBI6662: 1.5A output current

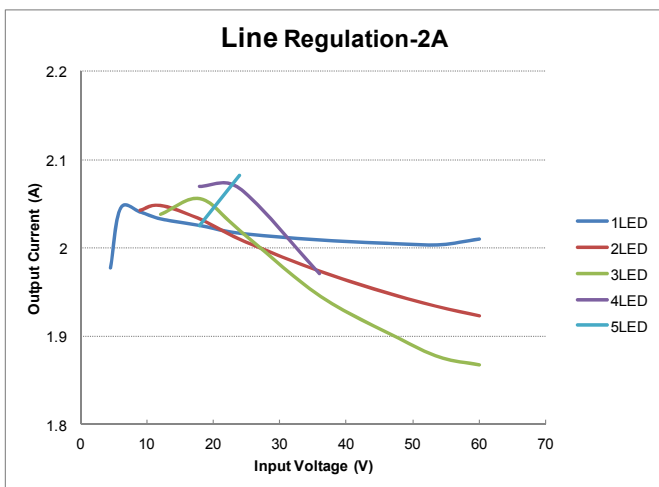


Fig.9 Line regulation of MBI6662: 2A output current

**Output Current vs. Temperature Variation**

$V_{IN}=12V$ , 1 LED,  $R_{CSP}=R_{CSN}=50m\Omega$ ,  $R_{FS}=300k\Omega$ ,  $L=68\mu H$ ,  $C_{COMP}=4.7nF$ ,  $C_{VCC}=1\mu F$ ,  $C_{IN}=10\mu F$ .

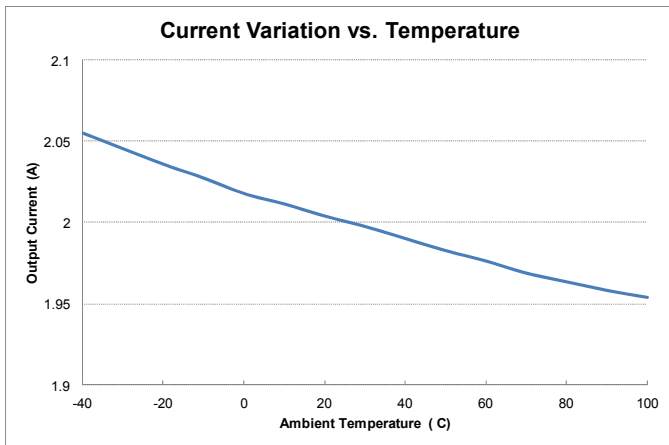


Fig.10 Output current variation with respect to temperature

**Output Current vs. Inductor Variation**

$V_{IN}=12V$ , 1 LED,  $R_{CSP}=R_{CSN}=50m\Omega$ ,  $R_{FS}=300k\Omega$ ,  $L=4.7\mu H\sim 100\mu H$ ,  $C_{COMP}=4.7nF$ ,  $C_{VCC}=1\mu F$ ,  $C_{IN}=10\mu F$ .

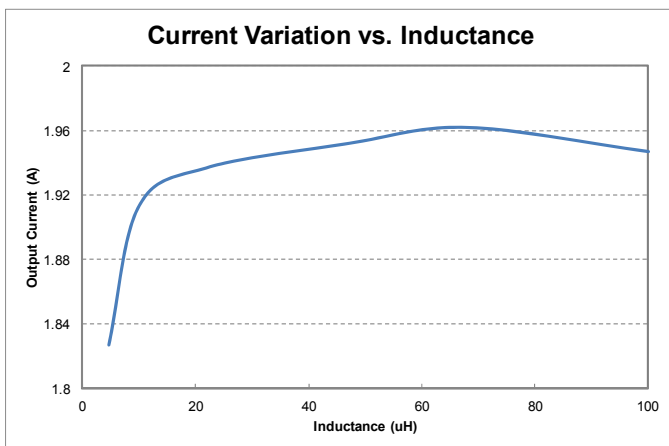


Fig.11 Output current variation with respect to inductance

**Dimming Linearity**

$V_{IN}=12V$ , 1 LED,  $R_{CSP}=R_{CSN}=50m\Omega$ ,  $R_{FS}=300k\Omega$ ,  $C_{COMP}=4.7nF$ ,  $C_{VCC}=1\mu F$ ,  $C_{IN}=10\mu F$ .

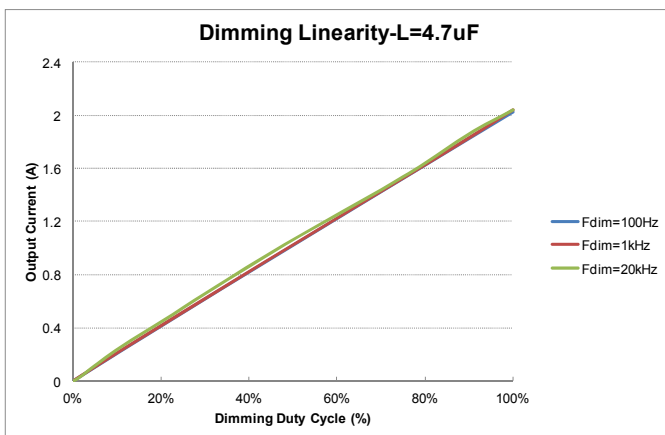


Fig.12 Dimming Linearity of MBI6662: L=4.7uH

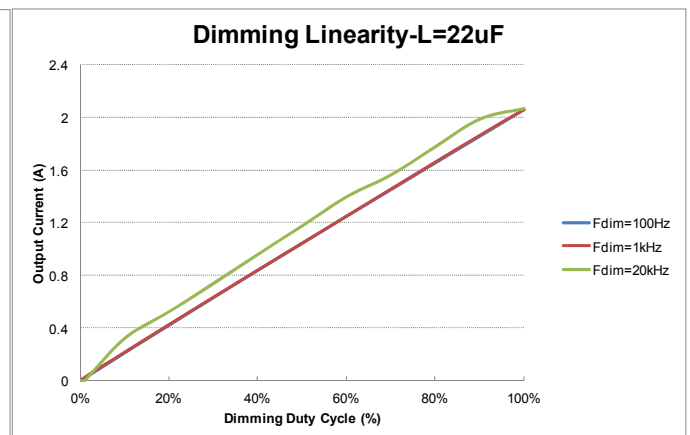


Fig.13 Dimming Linearity of MBI6662: L=22uH



Typical Switching Waveforms

$V_{IN}=12V$ ,  $V_{LED}=3.5V$ ,  $R_{CSP}=R_{CSN}=50m\Omega$  ( $I_{LED}=2A$ ),  $R_{FS}=300k\Omega$ ,  $L=4.7\mu\sim 100\mu H$ ,  $C_{COMP}=4.7nF$ ,  $C_{VCC}=1\mu F$ ,  $C_{IN}=10\mu F$ .

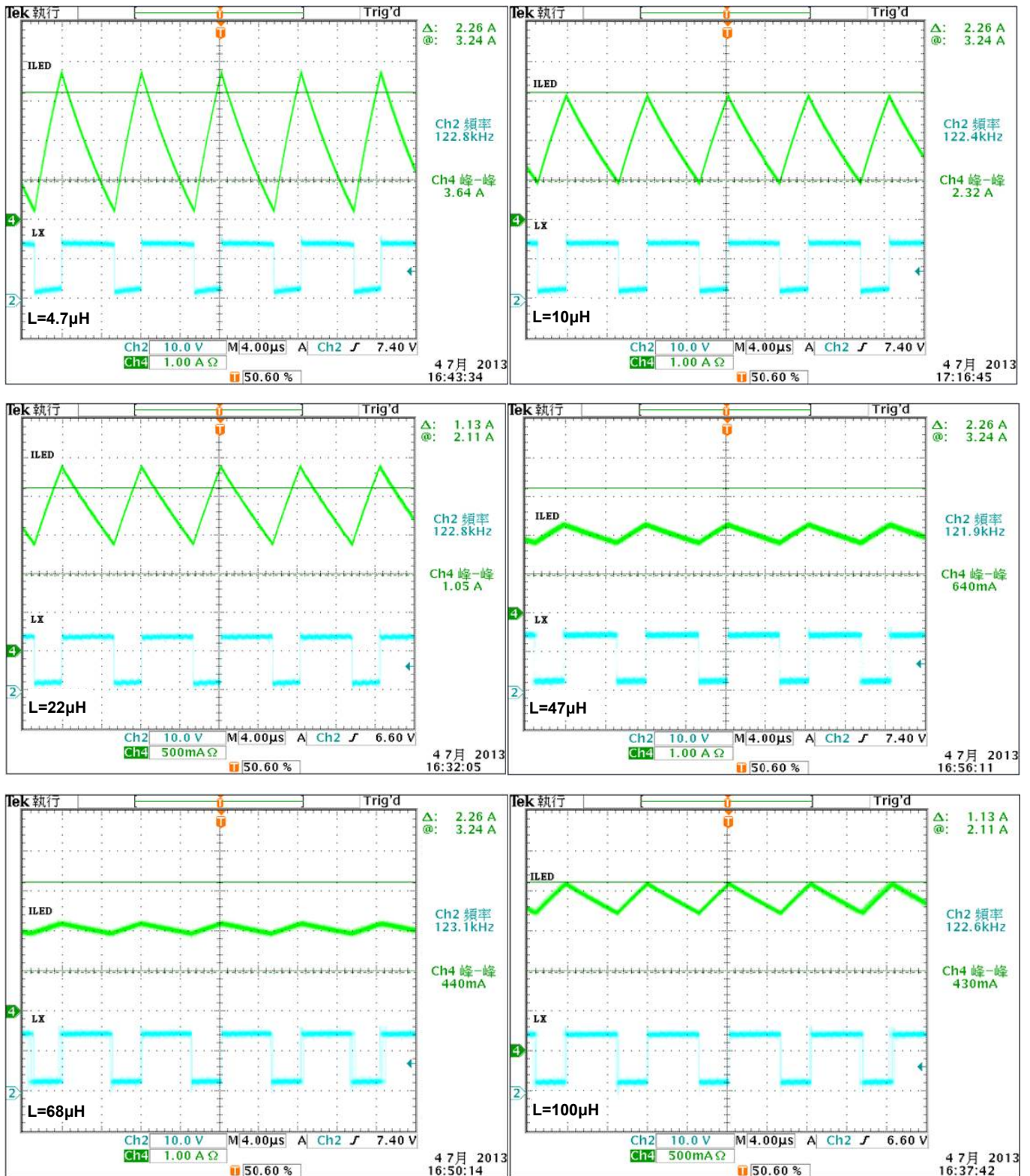


Fig.14 Typical switching waveforms of MBI6662: L=4.7 $\mu H$ ~100 $\mu H$

**Power On/Off Waveforms**

$V_{IN}=6V$ ,  $V_{LED}=3.5V$ ,  $R_{CSP}=R_{CSN}=50m\Omega$  ( $I_{LED}=2A$ ),  $R_{FS}=300k\Omega$ ,  $L=22\mu H$ ,  $C_{COMP}=4.7nF$ ,  $C_{VCC}=1\mu F$ ,  $C_{IN}=10\mu F$ .

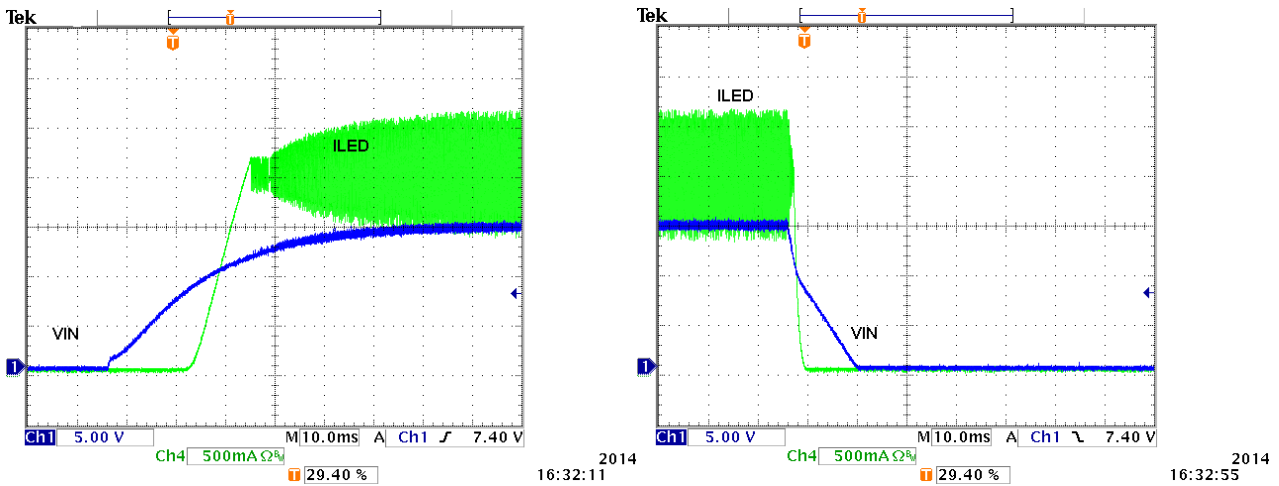


Fig.15 Power on/off waveforms of MBI6662

**Constant Switching Frequency Operation**

$R_{CSP}=R_{CSN}=50m\Omega$  ( $I_{LED}=2A$ ),  $R_{FS}=300k\Omega$ ,  $L=22\mu H/68\mu H$ ,  $C_{COMP}=4.7nF$ ,  $C_{VCC}=1\mu F$ ,  $C_{IN}=10\mu F$ .

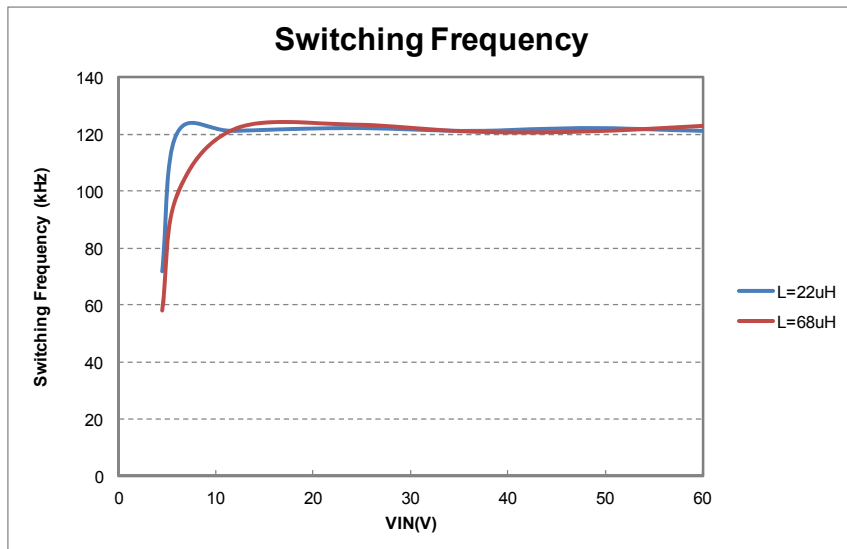


Fig.16 Constant switching frequency over wide input voltage range

Application Information

MBI6662 is a simple and high-efficiency buck converter with the capability of driving up to 2A current load. The adaptive hysteretic PFM control topology simplifies external circuit design to achieve constant frequency operation while possessing fast load transient response. The common-anode connection effectively reduces necessary wires in applications of multiple power modules in parallel. MBI6662 also equips with Under Voltage Lock-Out (UVLO), Over Temperature Protection (OTP), and Over Current Protection (OCP) to prevent the convertor from being damaged under abnormal operations.

Setting Output Current

In conventional hysteretic PFM topology, the switching frequency varies with input voltage and output loading. MBI6662 provides an innovative constant frequency technique to alleviate the sensitivity of switching frequency. From equation (1), ΔHYS must be adjustable to achieve constant frequency under various input voltage supposed inductance  $L_S$ ,  $V_{LED}$  and  $I_{LED}$  are fixed. In other words, MBI6662 dynamically adjusts the hysteretic window, ΔHYS, from 5% to 80% to achieve constant switching frequency.

$$f_s = \frac{(V_{IN} - V_{LED}) \frac{V_{LED}}{V_{IN}}}{\Delta I_{HYS} \times L \times I_{LED}} \dots\dots\dots (1)$$

where  $f_s$  is the switching frequency and  $\Delta HYS = \Delta I_{HYS} / I_{LED}$ , and  $\Delta I_{HYS}$  is the current variation in hysteretic control as shown in Fig.17.

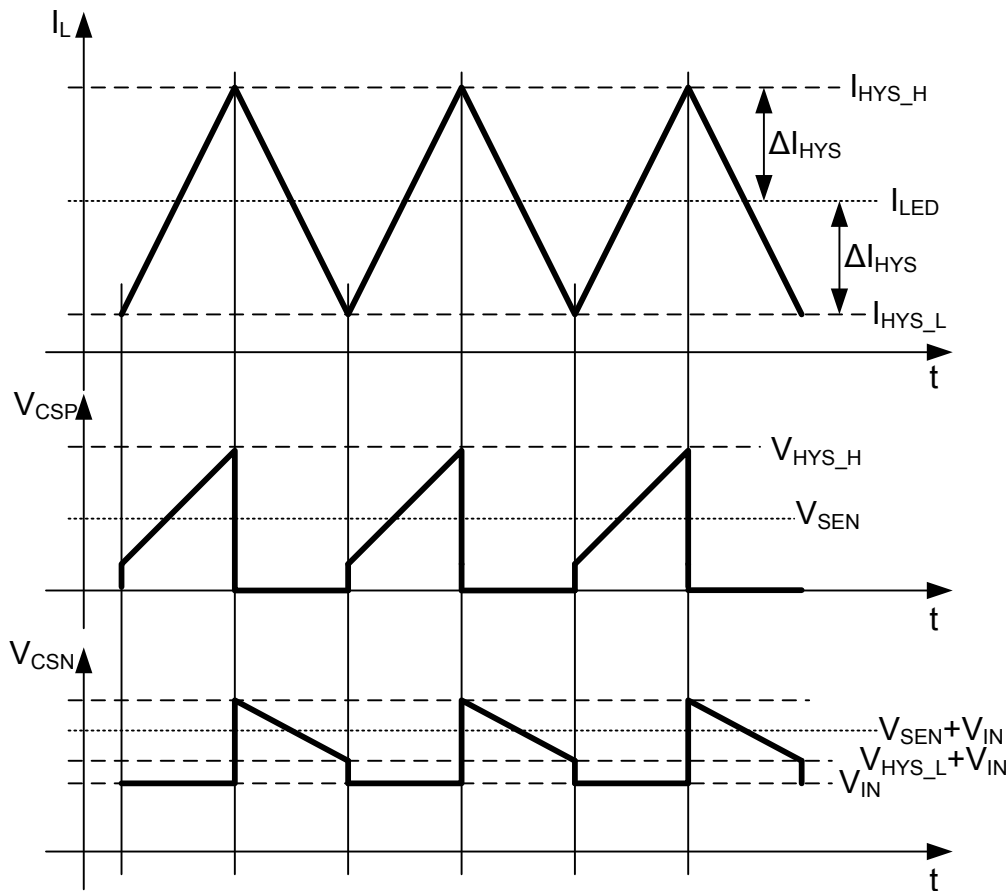


Fig.17 Typical switching waveforms of MBI6662

Fig.2 illustrates a typical application circuit of MBI6662. When the internal MOSFET is turned on, the inductor is charged by the dc power supply  $V_{IN}$ . The current flows through the loop composed of LED load, inductor  $L_S$ , internal MOSFET of MBI6662 and then return to GND through  $R_{CSP}$ . The voltage across  $R_{CSP}$ , i.e.  $V_{CSP}$ , increases with the charging inductor current, and the charging half cycle ends once  $V_{CSP}$  exceeds the upper threshold  $V_{HYS\_H}$ . The internal MOSFET will be turned off, and the inductor starts to discharge. The current circulates in loop of inductor  $L_S$ , freewheel diode  $D_S$ ,  $R_{CSN}$ , and the LED load.  $V_{CSN}$  decreases with the discharging inductor current, and the discharging half cycle ends when  $V_{CSN}$  is lower than  $V_{HYS\_L}+V_{IN}$ , as depicted Fig.17.

From Fig.2 and Fig.17, the average output current  $I_{LED}$  can be calculated as

$$I_{LED} = \frac{1}{2}(I_{HYS\_H} + I_{HYS\_L}) = \frac{1}{2} \left( \frac{V_{HYS\_H}}{R_{CSP}} + \frac{V_{HYS\_L}}{R_{CSN}} \right) \dots\dots\dots (2)$$

where

$$\begin{aligned} V_{HYS\_H} &= (1 + \Delta HYS) \times V_{SEN} \\ V_{HYS\_L} &= (1 - \Delta HYS) \times V_{SEN} \end{aligned} \dots\dots\dots (3)$$

And, therefore, the output LED current is calculated as

$$I_{LED} = \frac{V_{SEN}}{2} \left( \frac{(1 + \Delta HYS)}{R_{CSP}} + \frac{(1 - \Delta HYS)}{R_{CSN}} \right) \dots\dots\dots (4)$$

In order to simplify equation (4), replace  $R_{CSP}$  and  $R_{CSN}$  with  $R_{SEN}$ , and then the output current would be

$$I_{LED} = \frac{V_{SEN}}{R_{SEN}} \dots\dots\dots (5)$$

where  $V_{SEN}$  is the reference voltage 100mV, and  $R_{CSP}=R_{CSN}=R_{SEN}$ .

**Constant Frequency Control Scheme**

The switching frequency is set by an external resistor,  $R_{FS}$ , through pin FS. The internal control block compares the switching frequency to the preset reference frequency, and the hysteric window is adjusted accordingly to achieve constant switching frequency, as Fig.18 shows. Please refer to the “*MBI6662 Application Note*” and “*MBI6662 Design Tool*” of MBI6662 for detailed guidelines to properly set up the switching frequency for different applications.

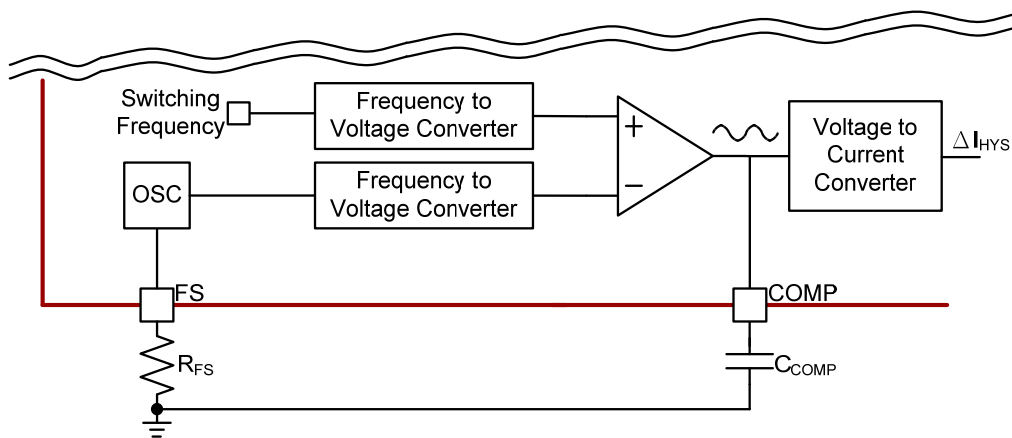


Fig.18 Constant frequency control scheme of MBI6662

**Common Anode Connection**

For conventional high-side sensing and low-side switching buck converters, the output LED string is not connected directly to the input power supply but through a sensing resistor. Therefore, when N such power modules work in parallel, each LED string possesses its unique anode voltage potential, and a total of 2N wires are necessary for these LED strings to be properly driven. MBI6662 supports common-anode connection, in which LED strings of the N parallel power modules share the same anode voltage potential, apparently the input voltage  $V_{IN}$ , and only N+1 wires are necessary to complete the wiring scheme.

**Dimming**

The dimming of LEDs can be performed by applying PWM signals at DIM pin. A logic low (below 0.8V) at DIM will disable the internal MOSFET and shut off the current flow to the LED array, whereas a logic high (above 2.5V) at DIM will resume the normal switching. An internal pull-up circuit ensures that MBI6662 is ON when DIM pin is unconnected. Fig.12 and Fig.13 illustrate comparisons of dimming performance for different inductor selections under various dimming frequency. Please refer to “*MBI6662 Application Note*” and “*MBI6662 Design Tool*” for proper setup of the dimming design.

**Under Voltage Lock Out Protection**

When the voltage at  $V_{IN}$  of MBI6662 is below 4.1V (typ.), the output current of MBI6662 is turned off. When the  $V_{IN}$  voltage of MBI6662 resumes to above 4.4V (typ.), the output current of MBI6662 is turned on again.

**LED Open-Circuit Protection**

When any LED connected to MBI6662 is open-circuited, the output current of MBI6662 will be terminated to protect the output capacitor from voltage over-stress, as shown in Fig.19. Once the open-circuit failure is removed, MBI6662 will resume normal operation as depicted in Fig.20.

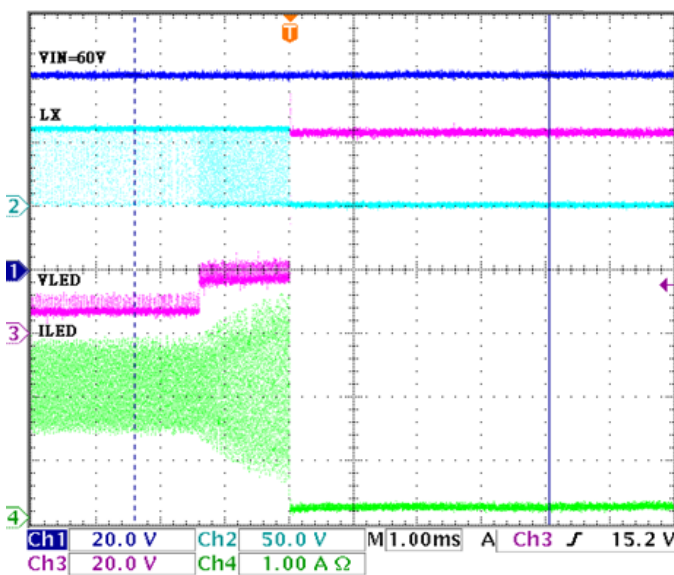


Fig.19 LED Open-Circuit Protection

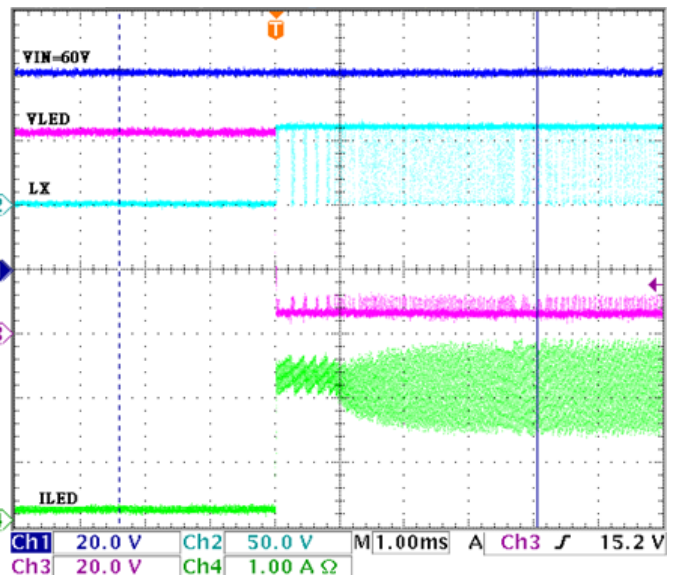


Fig.20 Open-circuit protection auto recovery



**LED Short-Circuit Protection**

When any LED connected to the MBI6662 is short-circuited, the output current of MBI6662 will be unaltered. If the whole LED string is short-circuited, which is equivalent that the pins VIN and LX are short, MBI6662 will turn off the MOSFET to protect the LEDs from being damaged by over-stress current. As depicted in Fig.21, the loop current is still in regulation at the preset level, and therefore the internal MOSFET keeps switching with minimum required on-time. Once the VIN-LX short condition is removed, MBI6662 resumes normal operation illustrated in Fig.22.

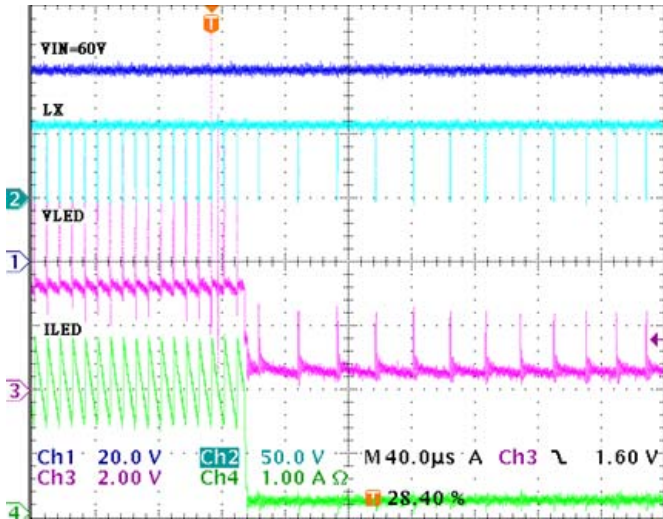


Fig.21 LED Short-Circuit Protection

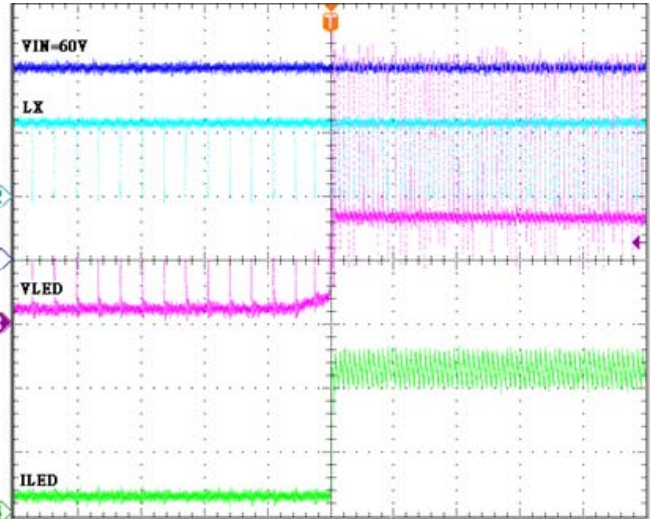


Fig.22 Short-circuit protection auto recovery

**Over Current Protection**

MBI6662 offers over current protection to eliminate irrecoverable damage resulting from abnormal excessive current, such as thermal runaway of the freewheel diode. The function is activated when the LED current reaches the threshold of 3A. The integrated MOSFET of MBI6662 will be turned off, and it will only resume normal operation when the input power supply is reset.

**Thermal Shutdown (TSD)**

When the junction temperature,  $T_j$ , exceeds the threshold of 155°C, TSD function turns off the output current by disabling the internal MOSFET. The junction temperature starts to decrease accordingly, and once the temperature drops below 125°C, the internal MOSFET turns on again and the converter resumes normal operation.

**Design Consideration**

The minimum inductance can be calculated by substituting an appropriate  $\Delta HYS$  in equation (1). To prevent the inductor current from exceeding the over current protection threshold ( $I_{OCP}$ ), as shown in Fig.24, it is recommended to set the  $\Delta HYS$  to be lower than half of the over current protection threshold, as illustrated in Fig.23. If the inductor peak current exceeds the  $I_{OCP}$ , OCP function will be triggered as stated in the previous section. Once the inductor valley current is under zero, as illustrated in Fig.25, the system operates in discontinuous conduction mode (DCM), in which the output current accuracy is degraded.

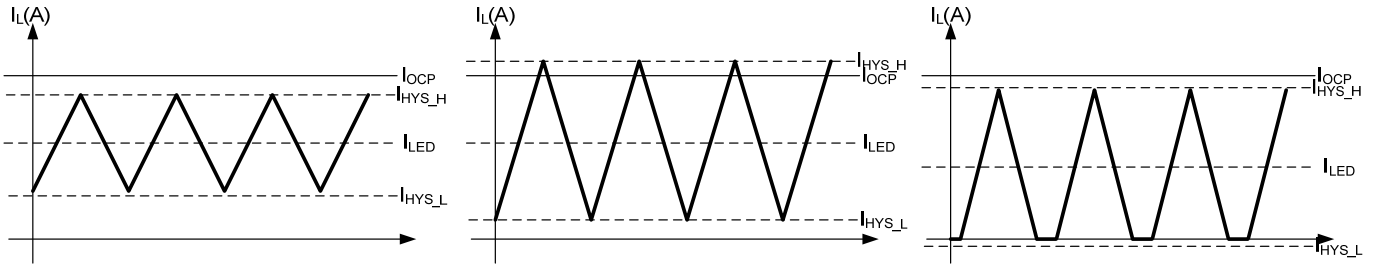


Fig.23 Normal setting ( $\Delta HYS < 0.5 \times I_{OCP}$ ) Fig.24 OCP trigger ( $I_{HYS\_H} < I_{OCP}$ ) Fig.25 DCM ( $I_{HYS\_L} < 0$ )

**Component Selection**

**Output Current Setup**

As shown in equation (5), the resistance of  $R_{SEN}$  is equal to  $V_{SEN}$  divided by  $I_{LED}$ , in which  $R_{SEN} = R_{CSP} = R_{CSN}$ .  $R_{CSP}$  and  $R_{CSN}$  are suggested to be implemented with resistors of 1% tolerance for better output current accuracy. The power dissipations of  $R_{SCP}$  and  $R_{CSN}$  are equal to  $P_{RSEN} = (V_{SEN}^2 / R_{SEN})$ , where  $V_{SEN}$  is equal to 100mV. To prevent the sustainable power from decreasing with the rising temperature, the rating of  $R_{CSP}$  and  $R_{CSN}$  is recommended to be 2.5 times of  $P_{RSEN}$ .

**Switching Frequency Setup**

The switching frequency is set by  $R_{FS}$  as illustrated in Fig.26. System efficiency and dimming resolution must be taken into consideration when setting the switching frequency. Given a high power application of 2A LED current, the recommended switching frequency is 100kHz considering the switching loss.

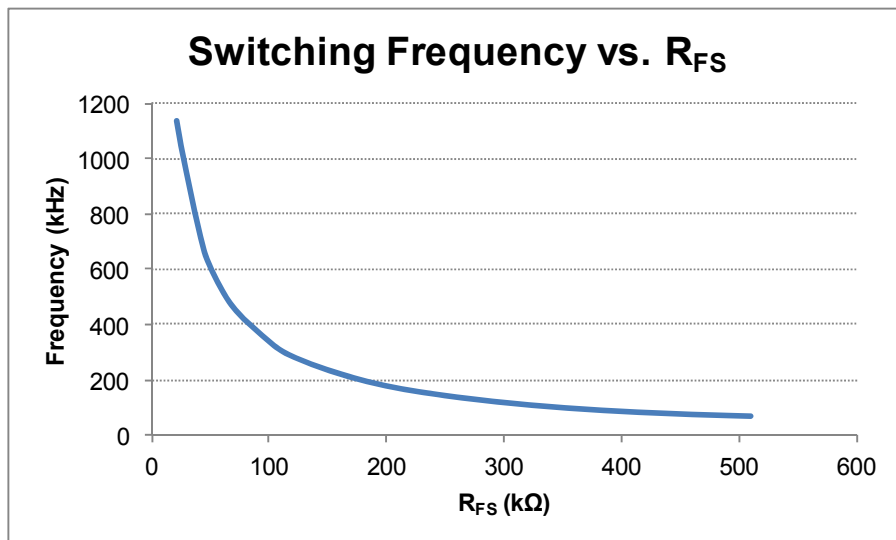


Fig.26 Switching frequency vs.  $R_{FS}$

**Inductor Selection**

After the switching frequency is determined, the inductance can be calculated by substituting the desired  $\Delta H_{YS}$  in equation (1). However, inductance is not only a concern of inductance but also the saturation current. The recommended saturation current should be at least 1.25 times of the inductor peak current  $I_{HYS\_H}$ . Moreover, the larger inductance results in better line and load regulations with the trade-off of smaller saturation current of the same size of inductor cores. Furthermore, the inductor with shielding is highly recommended for EMI consideration.

**Input Capacitor Selection**

Input capacitor provides instantaneous current to the converter when the internal MOSFET turns on, and also it is recharged by the input power supply when the internal MOSFET turns off. A capacitor of 10 $\mu$ F is preferred and the capacitance can be adjusted by applications. The rating voltage of the input capacitor is 1.5 times of the input voltage.

The advantages of electrolytic capacitor are cheap and easily accessible; on the other hand, the relatively short life time under high ambient temperature is its disadvantage. Small size, low ESR and good high frequency characteristic are the advantages of ceramic capacitor, but the need of supplementary transient voltage suppressor (TVS) to suppress the surge current during hot plug is its major drawback. Please refer to the "MBI6662 Application Note" for detailed guideline for choices of the appropriate type of capacitors.

**Schottky Diode Selection**

When the internal MOSFET turns off, the inductor discharges through the free-wheeling diode and LED to form a current loop. The Schottky diode with low forward voltage and fast response time is recommended for the choice of the free-wheeling diode. One consideration for the choice of an appropriate Schottky diode is the maximum reverse voltage, of which rating is 1.5 times of the input voltage; the other is the maximum forward current, and empirically 1.25 times of inductor peak current ( $I_{peak}$ ) is recommended.

**C<sub>COMP</sub> Selection**

MBI6662 only needs a compensation capacitor to adjust the response of the converter. The larger capacitance results in slower response time, and the smaller capacitance results in more obvious jitter-like transient response. The recommended C<sub>COMP</sub> capacitance is 4.7nF for most applications.

**C<sub>VCC</sub> Selection**

C<sub>VCC</sub> provides the transient current to the gate driver and the recommended capacitance is 1 $\mu$ F. The capacitance can be increased in low input voltage applications to prevent the VCC from dropping below UVLO and the accompanying undesirable restarting of the converter.

**Output Capacitor Selection (Optional)**

The output capacitor is used for reduction of the output ripple current. The larger capacitance results in smaller ripple current. The recommended capacitance is 10 $\mu$ F and the rating voltage is 1.5 times of the output voltage. The output capacitor also influences on the dimming resolution. In applications of high dimming resolution, the output capacitor is prohibited.



PCB Layout Consideration

Good PCB layout is helpful to enhance system performance. The guidelines are listed as follows.

1. Connect the pins of GND and GNDP to the negative terminal of input capacitor by a shortest possible trace. Keep the ground plane complete and DO NOT separate it into smaller portions.
2. To enhance the output current accuracy,  $R_{CSN}$  and  $R_{CSP}$  should be placed as close as possible to the CSN and CSP of IC through wider traces.
3. The input capacitor should be placed to the VIN pin as close as possible. If a close placement is not allowed, a  $0.1\mu F$  ceramic capacitor should be paralleled to the VIN and GND to serve as a bypass capacitor.
4. To prevent the noise interference originated from the internal MOSFET, reduce the PCB area which consists of SW pin, Schottky diode and the inductor.
5. In order to alleviate parasitic phenomena, the path with lager current flowing through should be short and wide.
6. When several LED modules work in parallel, the single-point grounding in parallel is recommended to prevent the interference to each others. Fig.27(a) shows the connection and the ground traces should be short and wide. The PCB layout of a multi-module application is shown in Fig.28.

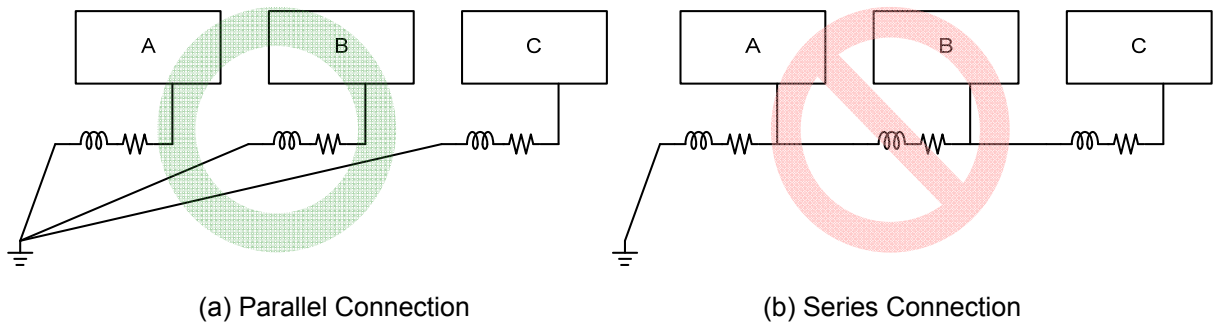


Fig.27 Single-point grounding methods

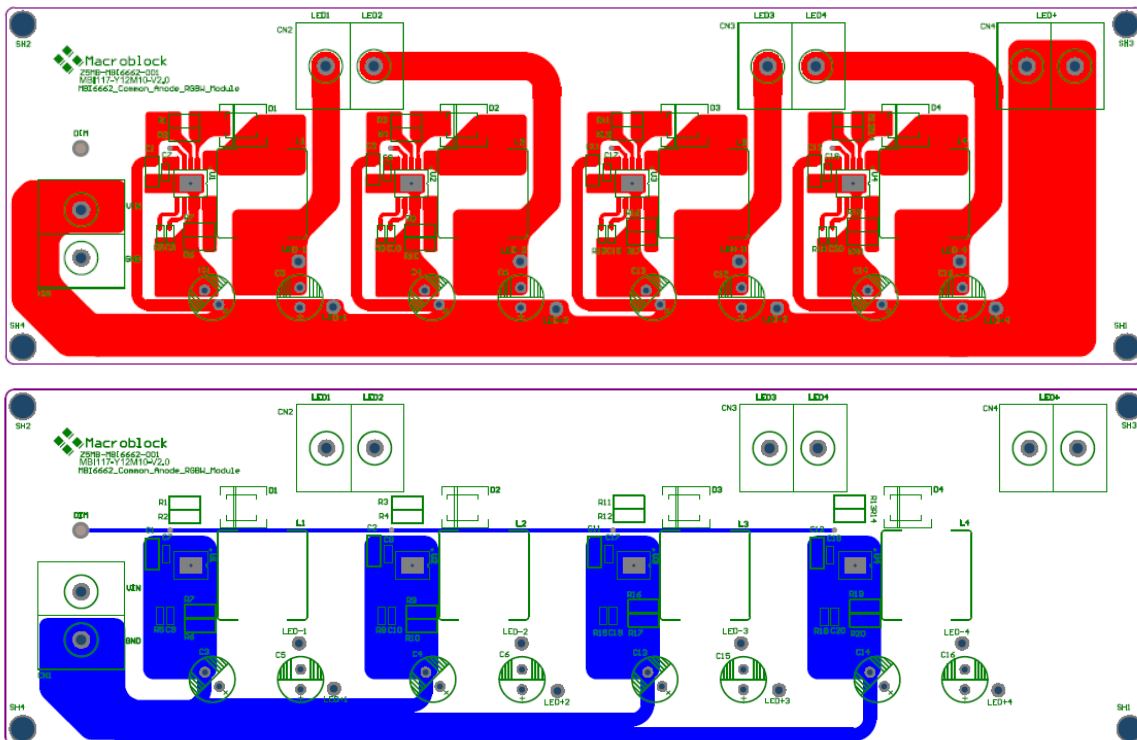
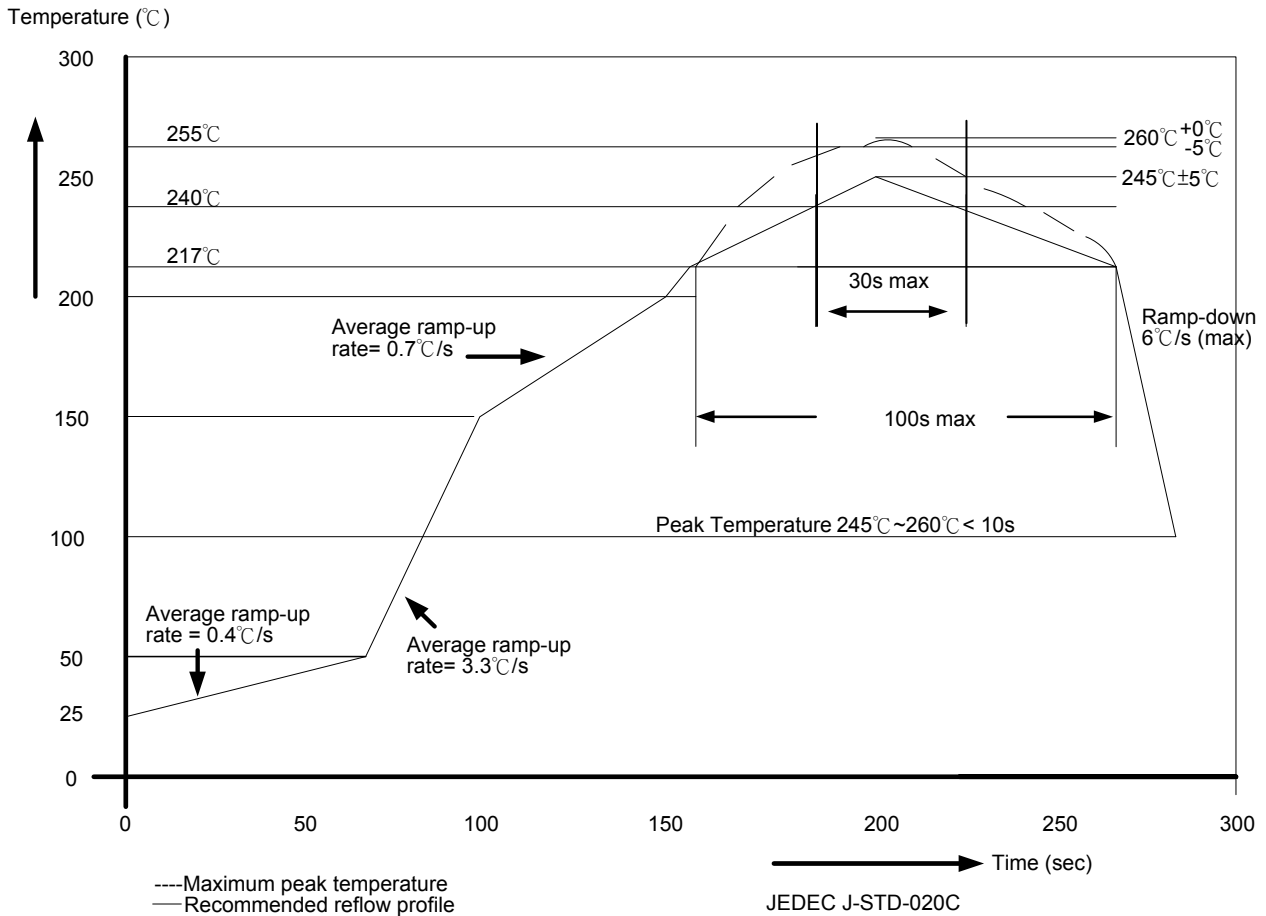


Fig.28 Sample layout of multi-module application of MBI6662

**Soldering Process of "Pb-free" Package Plating\***

Macroblock has defined "Pb-Free & Green" to mean semiconductor products that are compatible with the current RoHS requirements and selected 100% pure tin (Sn) to provide forward and backward compatibility with both the current industry-standard SnPb-based soldering processes and higher-temperature Pb-free processes. Pure tin is widely accepted by customers and suppliers of electronic devices in Europe, Asia and the US as the lead-free surface finish of choice to replace tin-lead. Also, it adopts tin/lead (SnPb) solder paste, and please refer to the JEDEC J-STD-020C for the temperature of solder bath. However, in the whole Pbfree soldering processes and materials, 100% pure tin (Sn) will all require from 245°C to 260°C for proper soldering on boards, referring to JEDEC J-STD-020C as shown below.

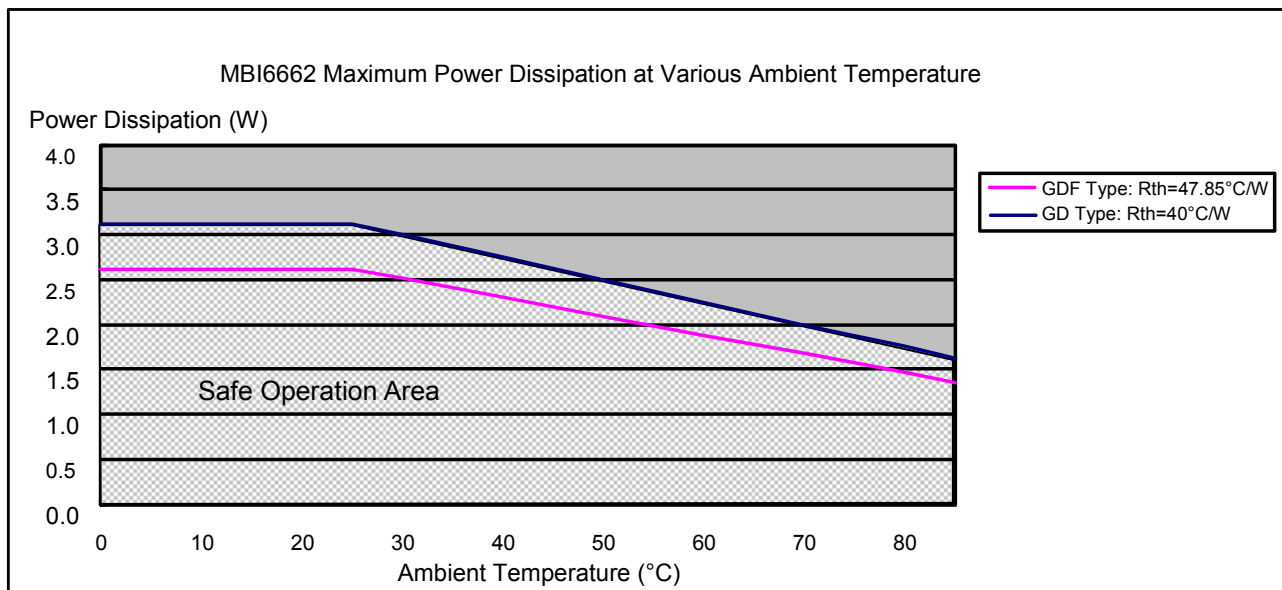


Package Thickness	Volume mm <sup>3</sup> <350	Volume mm <sup>3</sup> 350-2000	Volume mm <sup>3</sup> ≥ 2000
<1.6mm	260 +0 °C	260 +0 °C	260 +0 °C
1.6mm – 2.5mm	260 +0 °C	250 +0 °C	245 +0 °C
≥ 2.5mm	250 +0 °C	245 +0 °C	245 +0 °C

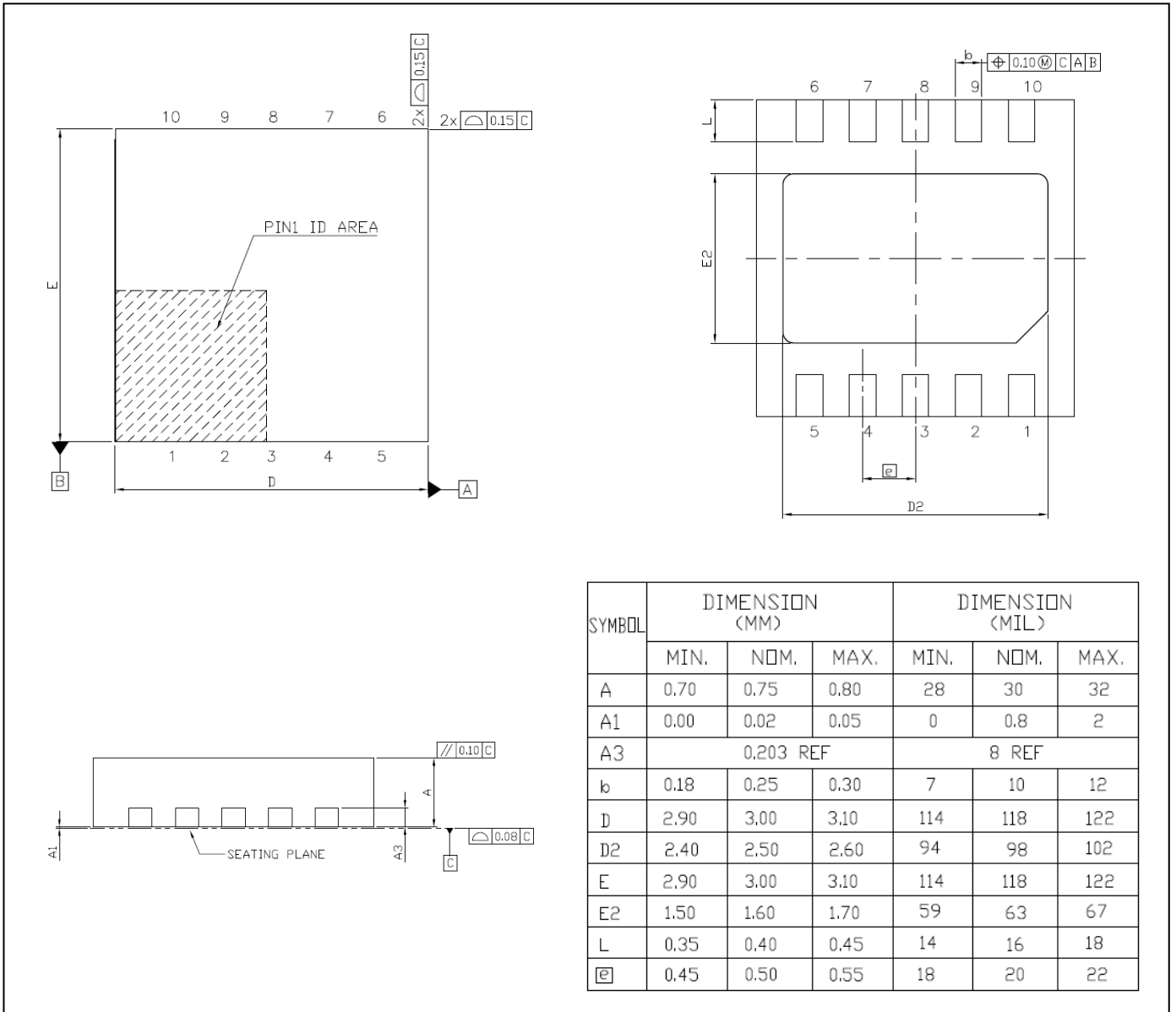
\* For details, please refer to Macroblock's "Policy on Pb-free & Green Package".

Package Power Dissipation (PD)

The maximum power dissipation,  $P_D(max)=(T_j-T_a)/R_{th(j-a)}$ , decreases as the ambient temperature increases.

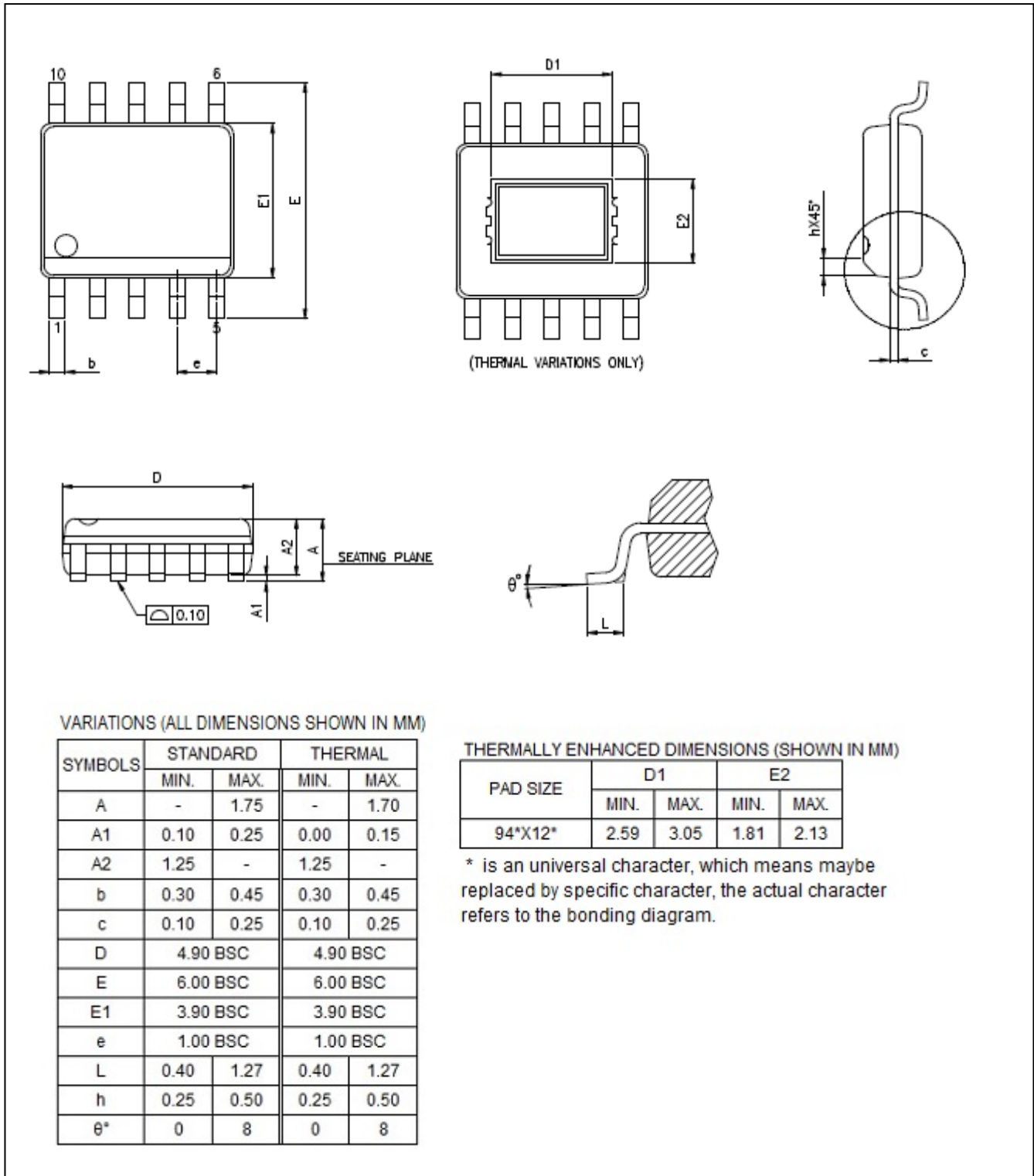


Outline Drawing



MBI6662GDF Outline Drawing

Note: Please use the maximum dimensions for the thermal pad layout. To avoid the short circuit risk, the vias or circuit traces shall not pass through the maximum area of thermal pad.

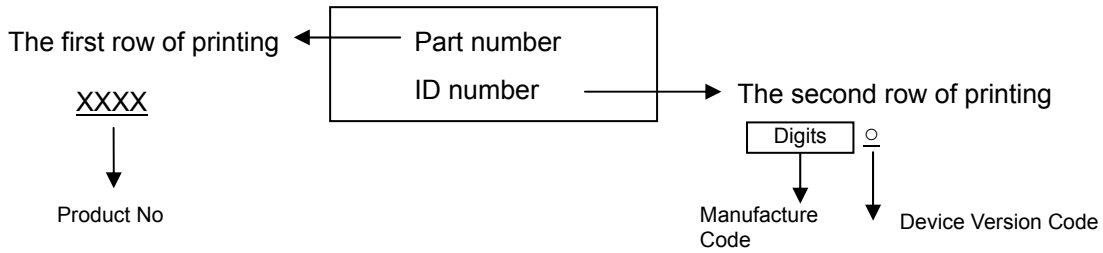


MBI6662GD Outline Drawing

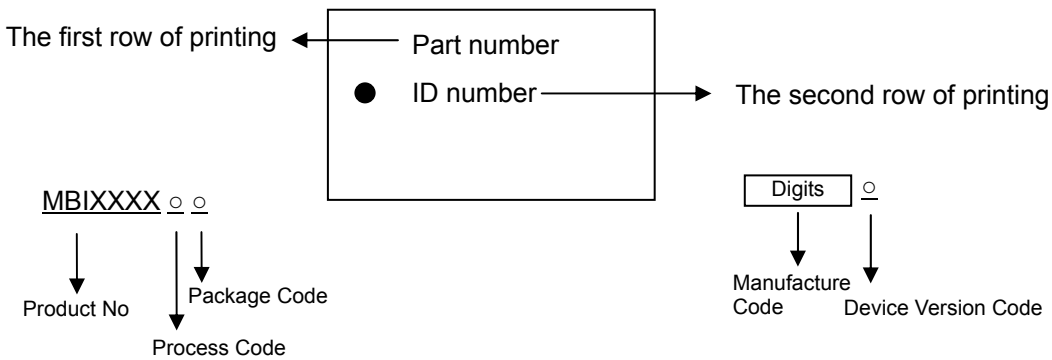
Note: Please use the maximum dimensions for the thermal pad layout. To avoid the short circuit risk, the vias or circuit traces shall not pass through the maximum area of thermal pad.

Product Top Mark Information

**GDF (DFN-10L)**



**GD(SOP-10L)**



Product Revision History

Datasheet version	Device Version Code
V1.00	A
V1.01	A

Product Ordering Information

Product Ordering Number*	RoHS Compliant Package Type	Weight (g)
MBI6662GDF-A	DFN-10L 3*3	0.02165
MBI6662GD-A	SOP-10L-150	0.0768

\*Please place your order with the “product ordering number” information on your purchase order (PO).

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